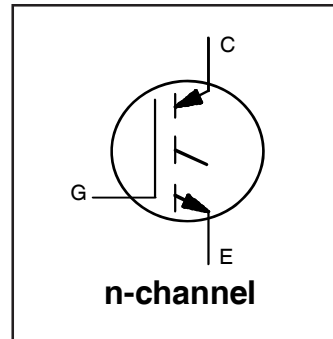


# IRG7PSH73K10PbF

## INSULATED GATE BIPOLAR TRANSISTOR

### Features

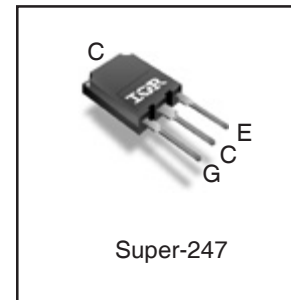
- Low  $V_{CE(ON)}$  Trench IGBT Technology
- Low Switching Losses
- Maximum Junction Temperature 175 °C
- 10  $\mu$ S short Circuit SOA
- Square RBSOA
- 100% of The Parts Tested for  $I_{LM}$
- Positive  $V_{CE(ON)}$  Temperature Coefficient
- Tight Parameter Distribution
- Lead Free Package



|                                                  |
|--------------------------------------------------|
| $V_{CES} = 1200V$                                |
| $I_{C(Nominal)} = 75A$                           |
| $t_{SC} \geq 10\mu s, T_{J(max)} = 175^{\circ}C$ |
| $V_{CE(on)} \text{ typ.} = 2.0V$                 |

### Benefits

- High Efficiency in a Wide Range of Applications
- Suitable for a Wide Range of Switching Frequencies due to Low  $V_{CE(ON)}$  and Low Switching Losses
- Rugged Transient Performance for Increased Reliability
- Excellent Current Sharing in Parallel Operation



| G    | C         | E       |
|------|-----------|---------|
| Gate | Collector | Emitter |

### Absolute Maximum Ratings

|                            | Parameter                                      | Max.                              | Units       |
|----------------------------|------------------------------------------------|-----------------------------------|-------------|
| $V_{CES}$                  | Collector-to-Emitter Voltage                   | 1200                              | V           |
| $I_C @ T_C = 25^{\circ}C$  | Continuous Collector Current                   | 220①                              | A           |
| $I_C @ T_C = 100^{\circ}C$ | Continuous Collector Current                   | 130                               |             |
| $I_{NOMINAL}$              | Nominal Current                                | 75                                |             |
| $I_{CM}$                   | Pulse Collector Current, $V_{GE}=15V$          | 225                               |             |
| $I_{LM}$                   | Clamped Inductive Load Current, $V_{GE}=20V$ ② | 300                               |             |
| $V_{GE}$                   | Continuous Gate-to-Emitter Voltage             | $\pm 30$                          | V           |
| $P_D @ T_C = 25^{\circ}C$  | Maximum Power Dissipation                      | 1150                              | W           |
| $P_D @ T_C = 100^{\circ}C$ | Maximum Power Dissipation                      | 580                               |             |
| $T_J$                      | Operating Junction and                         | -55 to +175                       | $^{\circ}C$ |
| $T_{STG}$                  | Storage Temperature Range                      |                                   |             |
|                            | Soldering Temperature, for 10 sec.             | 300 (0.063 in. (1.6mm) from case) |             |
|                            | Mounting Torque, 6-32 or M3 Screw              | 10 lbf-in (1.1 N·m)               |             |

### Thermal Resistance

|                        | Parameter                                                      | Min. | Typ. | Max. | Units         |
|------------------------|----------------------------------------------------------------|------|------|------|---------------|
| $R_{\theta JC}$ (IGBT) | Thermal Resistance Junction-to-Case-(each IGBT) ③              | —    | —    | 0.13 | $^{\circ}C/W$ |
| $R_{\theta CS}$        | Thermal Resistance, Case-to-Sink (flat, greased surface) ③     | —    | 0.24 | —    |               |
| $R_{\theta JA}$        | Thermal Resistance, Junction-to-Ambient (typical socket mount) | —    | 40   | —    |               |

## Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

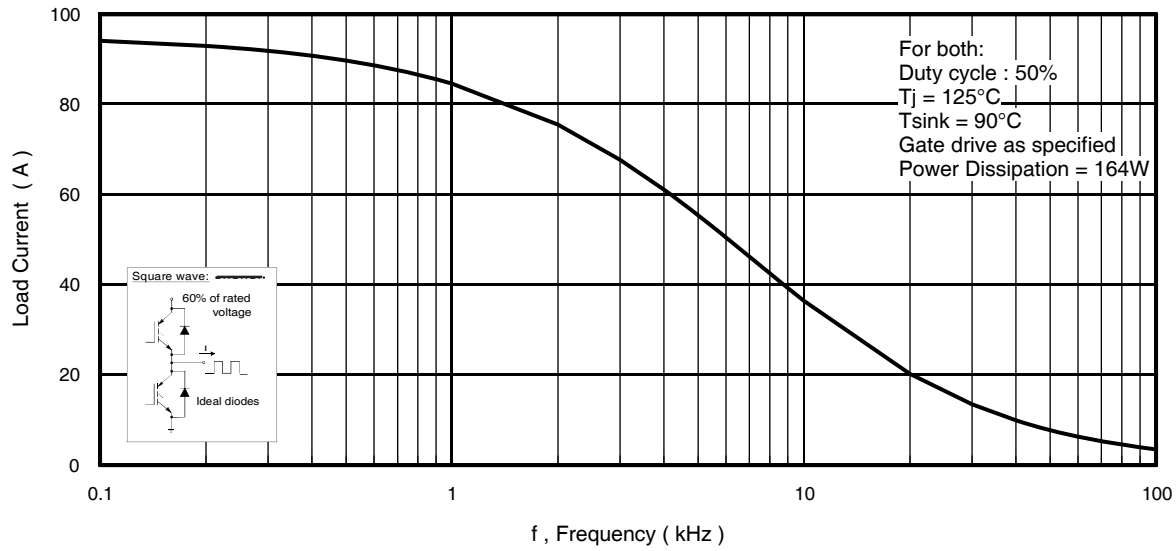
|                                 | Parameter                               | Min. | Typ. | Max.      | Units   | Conditions                                             |
|---------------------------------|-----------------------------------------|------|------|-----------|---------|--------------------------------------------------------|
| $V_{(BR)CES}$                   | Collector-to-Emitter Breakdown Voltage  | 1200 | —    | —         | V       | $V_{GE} = 0V, I_C = 250\mu A$ ④                        |
| $\Delta V_{(BR)CES}/\Delta T_J$ | Temperature Coeff. of Breakdown Voltage | —    | 1.58 | —         | V/°C    | $V_{GE} = 0V, I_C = 5.0mA$ (25°C-175°C) ④              |
| $V_{CE(on)}$                    | Collector-to-Emitter Saturation Voltage | —    | 2.0  | 2.3       | V       | $I_C = 75A, V_{GE} = 15V, T_J = 25^\circ\text{C}$ ③    |
|                                 |                                         | —    | 2.50 | —         |         | $I_C = 75A, V_{GE} = 15V, T_J = 150^\circ\text{C}$ ③   |
|                                 |                                         | —    | 2.60 | —         |         | $I_C = 75A, V_{GE} = 15V, T_J = 175^\circ\text{C}$ ③   |
| $V_{GE(th)}$                    | Gate Threshold Voltage                  | 5.0  | —    | 7.5       | V       | $V_{CE} = V_{GE}, I_C = 3.5mA$                         |
| $\Delta V_{GE(th)}/\Delta T_J$  | Threshold Voltage temp. coefficient     | —    | -18  | —         | mV/°C   | $V_{CE} = V_{GE}, I_C = 3.5mA$ (25°C - 175°C)          |
| $g_{fe}$                        | Forward Transconductance                | —    | 53   | —         | S       | $V_{CE} = 50V, I_C = 75A, PW = 80\mu s$                |
| $I_{CES}$                       | Collector-to-Emitter Leakage Current    | —    | 1.0  | 25        | $\mu A$ | $V_{GE} = 0V, V_{CE} = 1200V, T_J = 25^\circ\text{C}$  |
|                                 |                                         | —    | 2340 | —         |         | $V_{GE} = 0V, V_{CE} = 1200V, T_J = 175^\circ\text{C}$ |
| $I_{GES}$                       | Gate-to-Emitter Leakage Current         | —    | —    | $\pm 400$ | nA      | $V_{GE} = \pm 30V$                                     |

## Switching Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

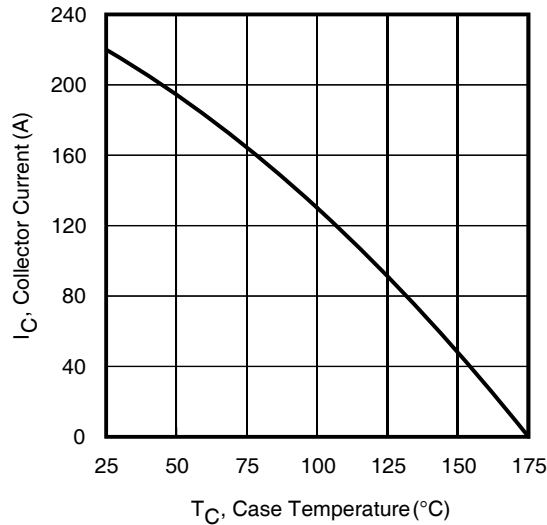
|              | Parameter                          | Min.        | Typ. | Max. | Units   | Conditions                                                                                                        |
|--------------|------------------------------------|-------------|------|------|---------|-------------------------------------------------------------------------------------------------------------------|
| $Q_g$        | Total Gate Charge (turn-on)        | —           | 360  | 540  | nC      | $I_C = 75A$ ③                                                                                                     |
| $Q_{ge}$     | Gate-to-Emitter Charge (turn-on)   | —           | 87   | 130  |         | $V_{GE} = 15V$                                                                                                    |
| $Q_{gc}$     | Gate-to-Collector Charge (turn-on) | —           | 180  | 270  |         | $V_{CC} = 600V$                                                                                                   |
| $E_{on}$     | Turn-On Switching Loss             | —           | 7.7  | 8.7  | mJ      | $I_C = 75A, V_{CC} = 600V, V_{GE} = 15V$ ③                                                                        |
| $E_{off}$    | Turn-Off Switching Loss            | —           | 4.6  | 5.6  |         | $R_G = 4.7\Omega, L = 200\mu H, T_J = 25^\circ\text{C}$                                                           |
| $E_{total}$  | Total Switching Loss               | —           | 12.3 | 14.3 |         | Energy losses include tail & diode reverse recovery                                                               |
| $t_{d(on)}$  | Turn-On delay time                 | —           | 63   | 81   | ns      | $I_C = 75A, V_{CC} = 600V, V_{GE} = 15V$ ③                                                                        |
| $t_r$        | Rise time                          | —           | 118  | 138  |         | $R_G = 4.7\Omega, L = 200\mu H, T_J = 25^\circ\text{C}$                                                           |
| $t_{d(off)}$ | Turn-Off delay time                | —           | 267  | 291  |         |                                                                                                                   |
| $t_f$        | Fall time                          | —           | 114  | 134  |         |                                                                                                                   |
| $E_{on}$     | Turn-On Switching Loss             | —           | 11   | —    | mJ      | $I_C = 75A, V_{CC} = 600V, V_{GE} = 15V$ ③                                                                        |
| $E_{off}$    | Turn-Off Switching Loss            | —           | 7.4  | —    |         | $R_G = 4.7\Omega, L = 200\mu H, T_J = 175^\circ\text{C}$                                                          |
| $E_{total}$  | Total Switching Loss               | —           | 18.4 | —    |         | Energy losses include tail & diode reverse recovery                                                               |
| $t_{d(on)}$  | Turn-On delay time                 | —           | 62   | —    | ns      | $I_C = 75A, V_{CC} = 600V, V_{GE} = 15V$ ③                                                                        |
| $t_r$        | Rise time                          | —           | 110  | —    |         | $R_G = 4.7\Omega, L = 200\mu H$                                                                                   |
| $t_{d(off)}$ | Turn-Off delay time                | —           | 330  | —    |         | $T_J = 175^\circ\text{C}$                                                                                         |
| $t_f$        | Fall time                          | —           | 237  | —    |         |                                                                                                                   |
| $C_{ies}$    | Input Capacitance                  | —           | 9450 | —    | pF      | $V_{GE} = 0V$                                                                                                     |
| $C_{oes}$    | Output Capacitance                 | —           | 340  | —    |         | $V_{CC} = 30V$                                                                                                    |
| $C_{res}$    | Reverse Transfer Capacitance       | —           | 230  | —    |         | $f = 1.0MHz$                                                                                                      |
| RBSOA        | Reverse Bias Safe Operating Area   | FULL SQUARE |      |      |         | $I_C = 300A$<br>$V_{CC} = 960V, V_p = 1200V$<br>$R_G = 4.7\Omega, V_{GE} = +20V$ to 0V, $T_J = 175^\circ\text{C}$ |
| SCSOA        | Short Circuit Safe Operating Area  | 10          | —    | —    | $\mu s$ | $V_{CC} = 600V, V_p = 1200V, T_J = 150^\circ\text{C}$<br>$R_G = 4.7\Omega, V_{GE} = +15V$ to 0V                   |

### Notes:

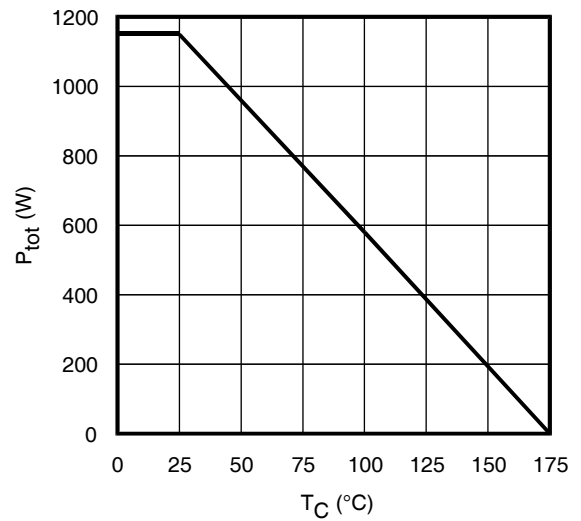
- ① Calculated continuous current based on maximum allowable junction temperature. Bond wire current limit is 195A. Note that current limitations arising from heating of the device leads may occur with some lead mounting arrangements. (Refer to AN-1140)
- ②  $V_{CC} = 80\% (V_{CES}), V_{GE} = 20V, L = 20\mu H, R_G = 5.0\Omega$ .
- ③ Pulse width  $\leq 400\mu s$ ; duty cycle  $\leq 2\%$ .
- ④ Refer to AN-1086 for guidelines for measuring  $V_{(BR)CES}$  safely.
- ⑤  $R_\theta$  is measured at  $T_J$  of approximately  $90^\circ\text{C}$ .



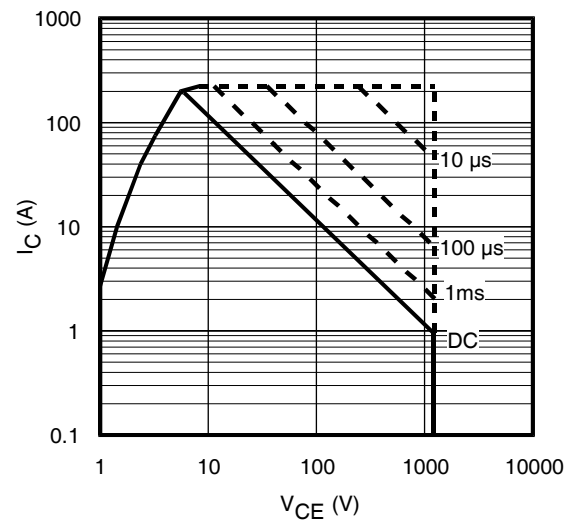
**Fig. 1 - Typical Load Current vs. Frequency**



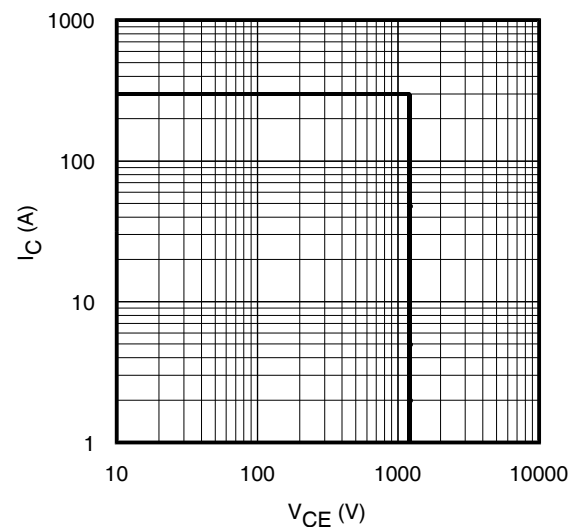
**Fig. 2 - Maximum DC Collector Current vs. Case Temperature**



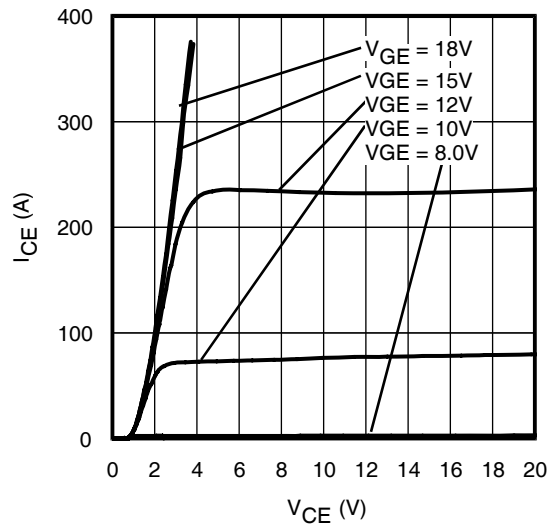
**Fig. 3 - Power Dissipation vs. Case Temperature**



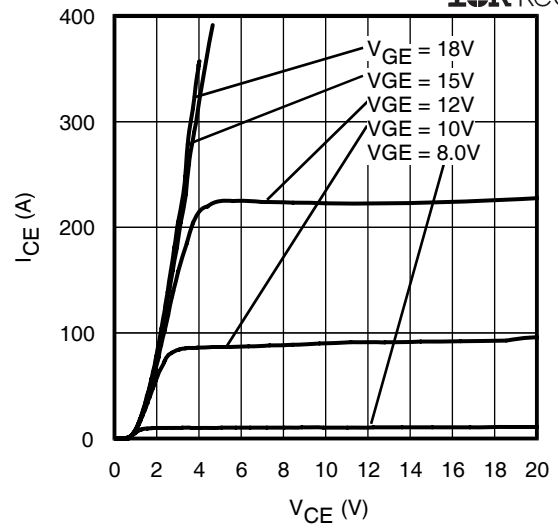
**Fig. 4 - Forward SOA**  
 $T_C = 25^{\circ}\text{C}$ ,  $T_J \leq 175^{\circ}\text{C}$ ;  $V_{GE} = 15\text{V}$



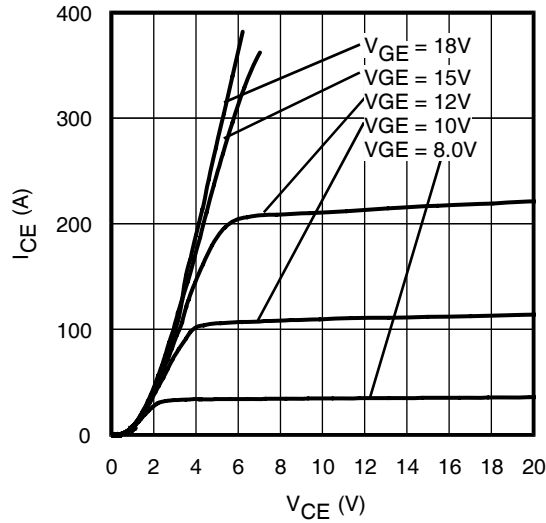
**Fig. 5 - Reverse Bias SOA**  
 $T_J = 175^{\circ}\text{C}$ ;  $V_{GE} = 20\text{V}$



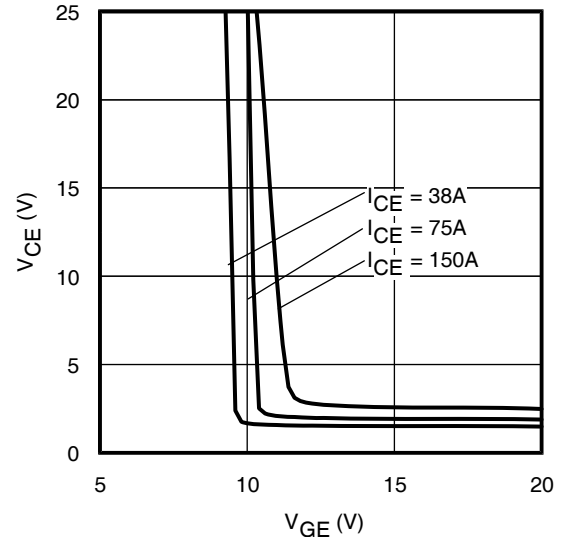
**Fig. 6** - Typ. IGBT Output Characteristics  
T<sub>J</sub> = -40°C; t<sub>p</sub> = 80μs



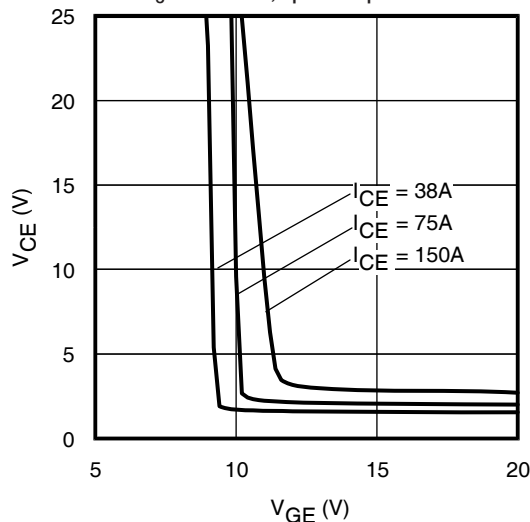
**Fig. 7** - Typ. IGBT Output Characteristics  
T<sub>J</sub> = 25°C; t<sub>p</sub> = 80μs



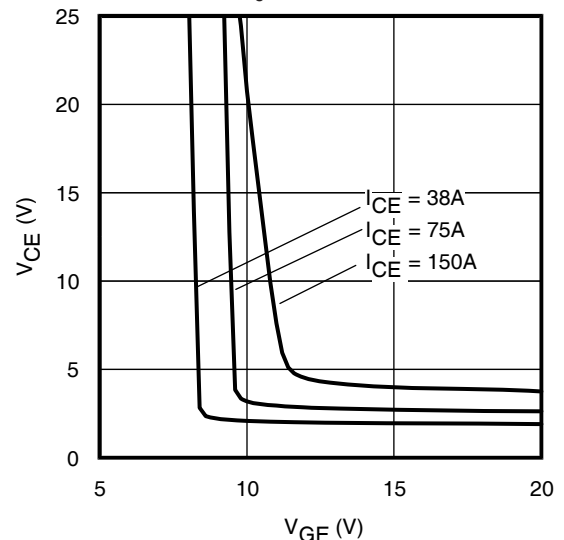
**Fig. 8** - Typ. IGBT Output Characteristics  
T<sub>J</sub> = 175°C; t<sub>p</sub> = 80μs



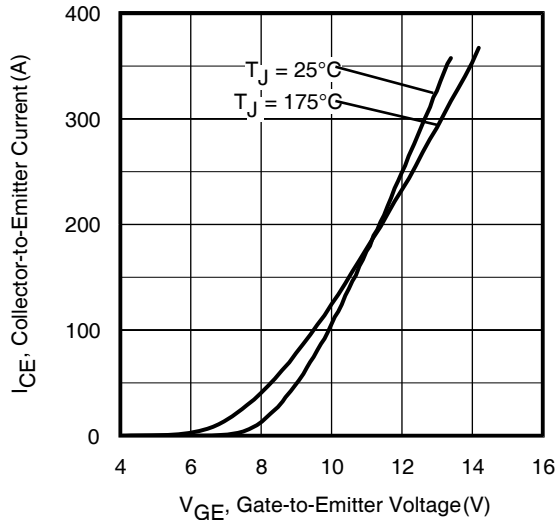
**Fig. 9** - Typical V<sub>CE</sub> vs. V<sub>GE</sub>  
T<sub>J</sub> = -40°C



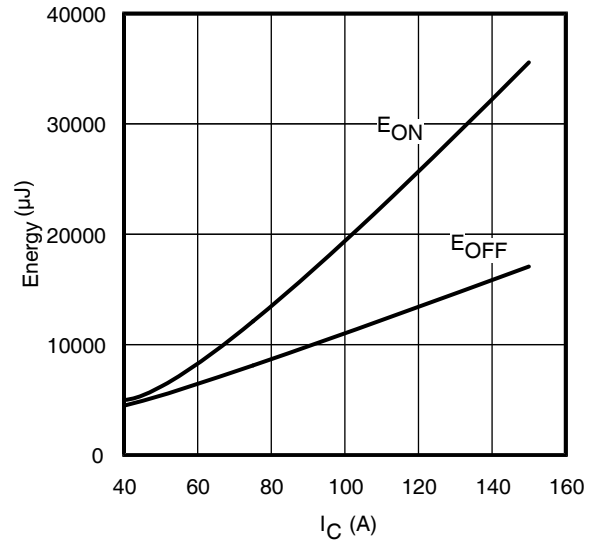
**Fig. 10** - Typical V<sub>CE</sub> vs. V<sub>GE</sub>  
T<sub>J</sub> = 25°C



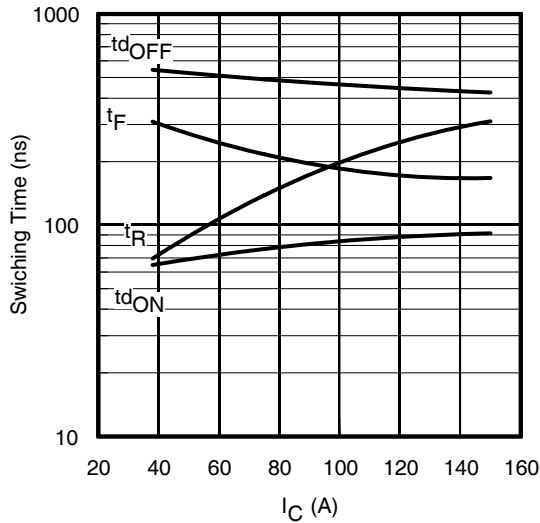
**Fig. 11** - Typical V<sub>CE</sub> vs. V<sub>GE</sub>  
T<sub>J</sub> = 175°C



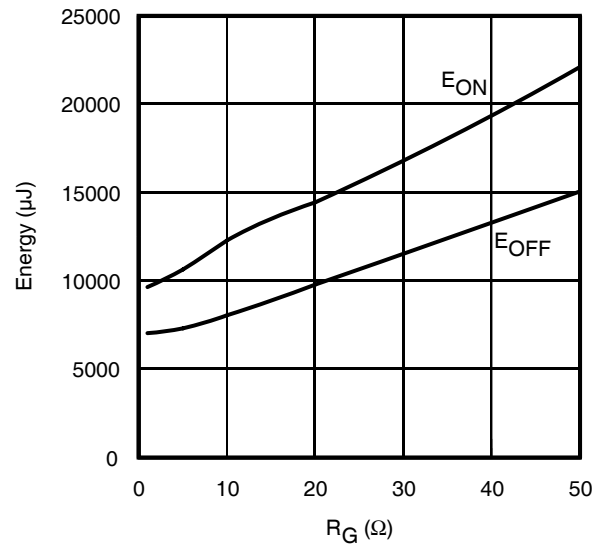
**Fig. 12 - Typ. Transfer Characteristics**  
 $V_{CE} = 50V$ ;  $t_p = 10\mu s$



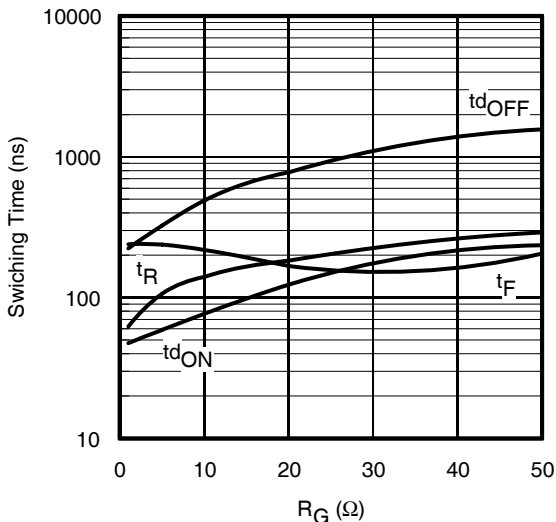
**Fig. 13 - Typ. Energy Loss vs.  $I_C$**   
 $T_J = 175^\circ C$ ;  $L = 200\mu H$ ;  $V_{CE} = 600V$ ,  $R_G = 5.0\Omega$ ;  $V_{GE} = 15V$



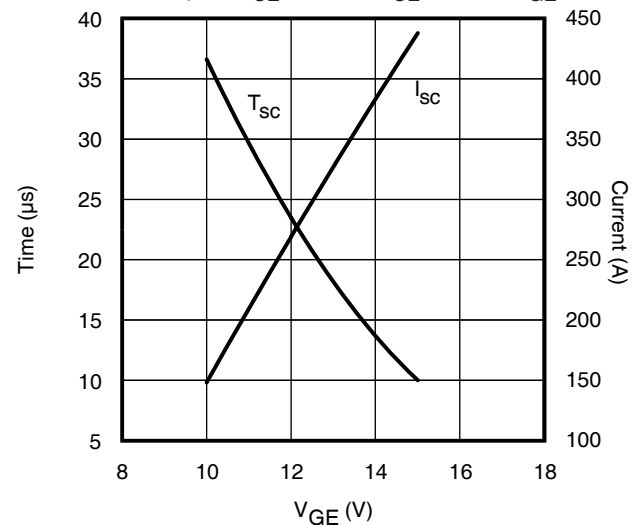
**Fig. 14 - Typ. Switching Time vs.  $I_C$**   
 $T_J = 175^\circ C$ ;  $L = 200\mu H$ ;  $V_{CE} = 600V$ ,  $R_G = 5.0\Omega$ ;  $V_{GE} = 15V$



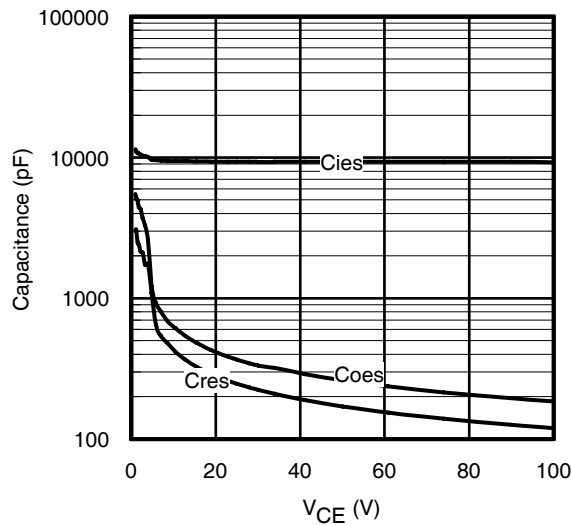
**Fig. 15 - Typ. Energy Loss vs.  $R_G$**   
 $T_J = 175^\circ C$ ;  $L = 200\mu H$ ;  $V_{CE} = 600V$ ,  $I_{CE} = 75A$ ;  $V_{GE} = 15V$



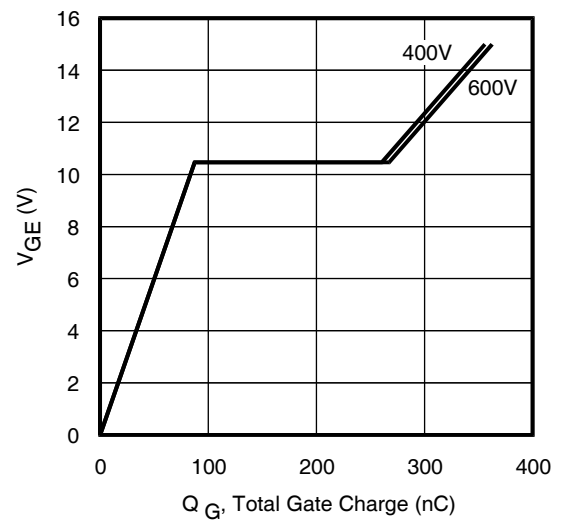
**Fig. 16 - Typ. Switching Time vs.  $R_G$**   
 $T_J = 175^\circ C$ ;  $L = 200\mu H$ ;  $V_{CE} = 600V$ ,  $I_{CE} = 75A$ ;  $V_{GE} = 15V$



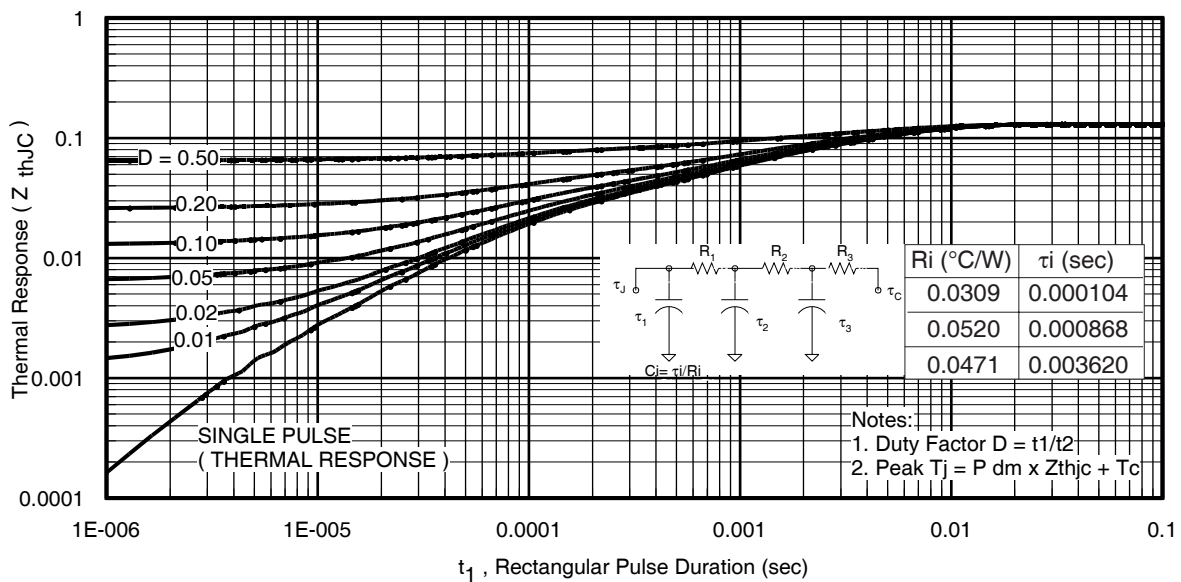
**Fig. 17 -  $V_{GE}$  vs. Short Circuit Time**  
 $V_{CC} = 600V$ ;  $T_C = 150^\circ C$



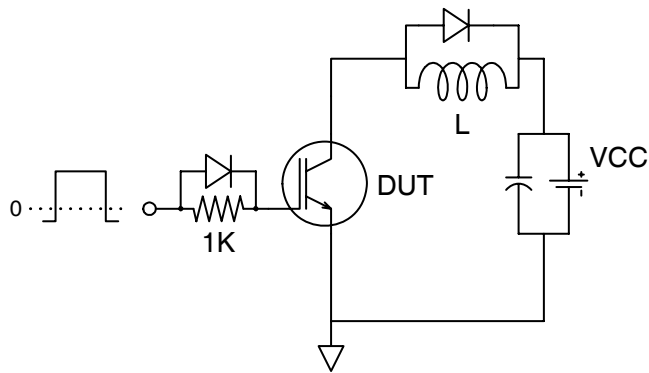
**Fig. 18** - Typ. Capacitance vs.  $V_{CE}$   
 $V_{GE} = 0V$ ;  $f = 1MHz$



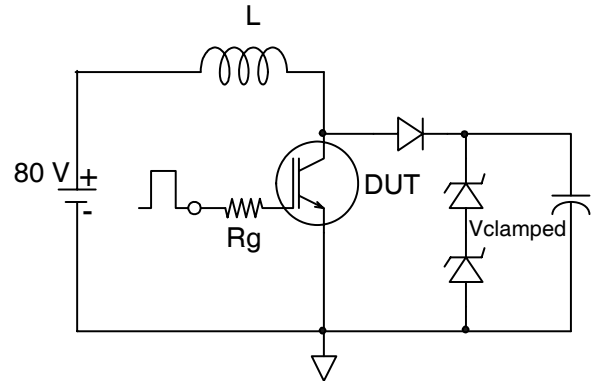
**Fig. 19** - Typical Gate Charge vs.  $V_{GE}$   
 $I_{CE} = 75A$ ;  $L = 330\mu H$



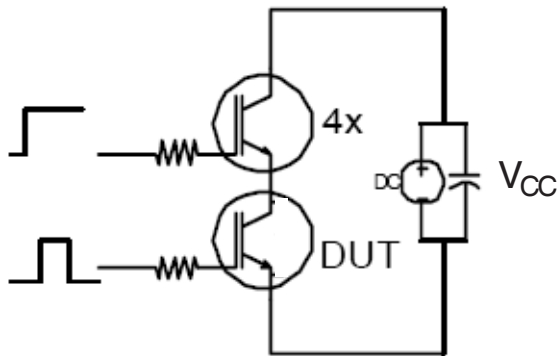
**Fig 20.** Maximum Transient Thermal Impedance, Junction-to-Case



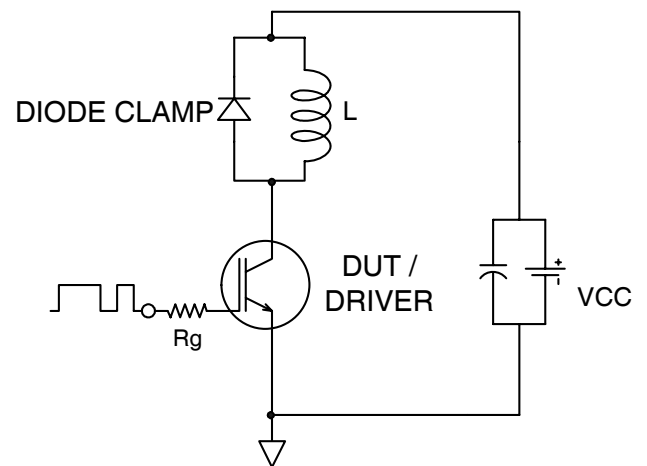
**Fig.C.T.1** - Gate Charge Circuit (turn-off)



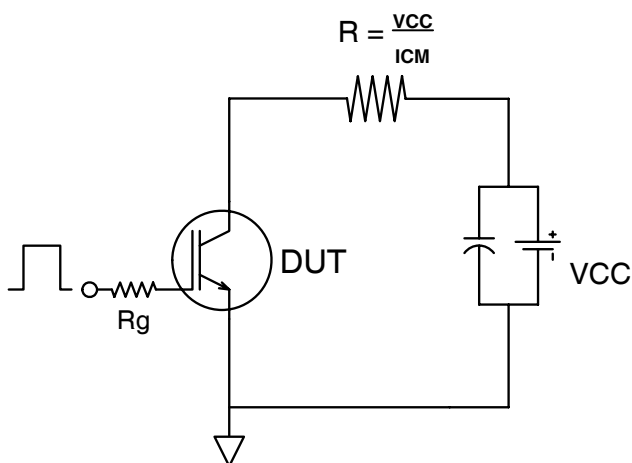
**Fig.C.T.2** - RBSOA Circuit



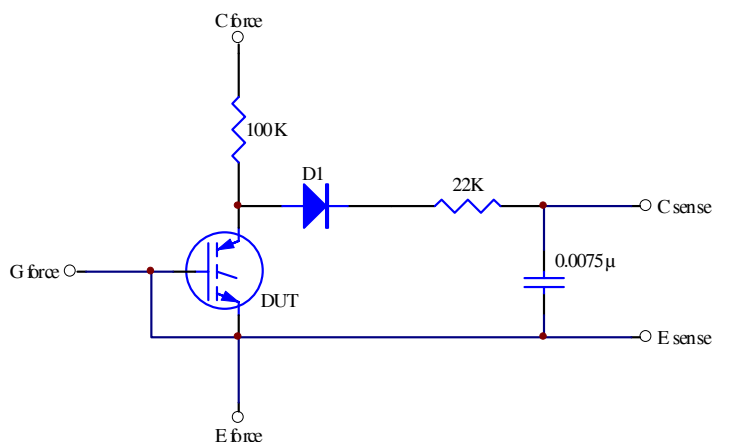
**Fig.C.T.3** - S.C. SOA Circuit



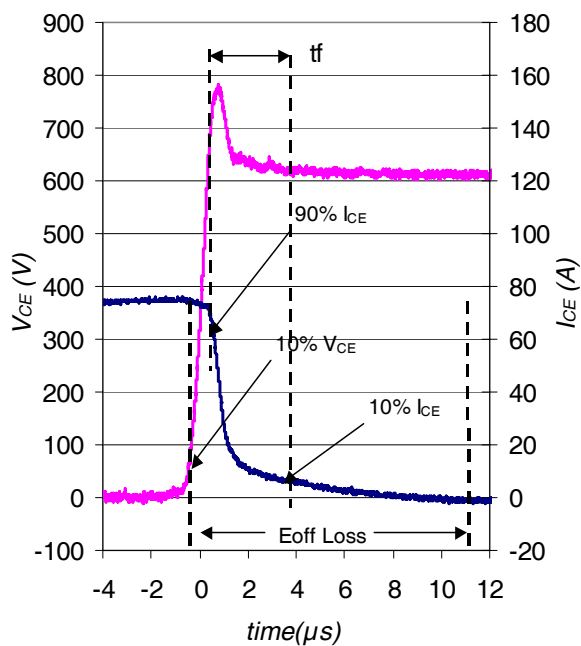
**Fig.C.T.4** - Switching Loss Circuit



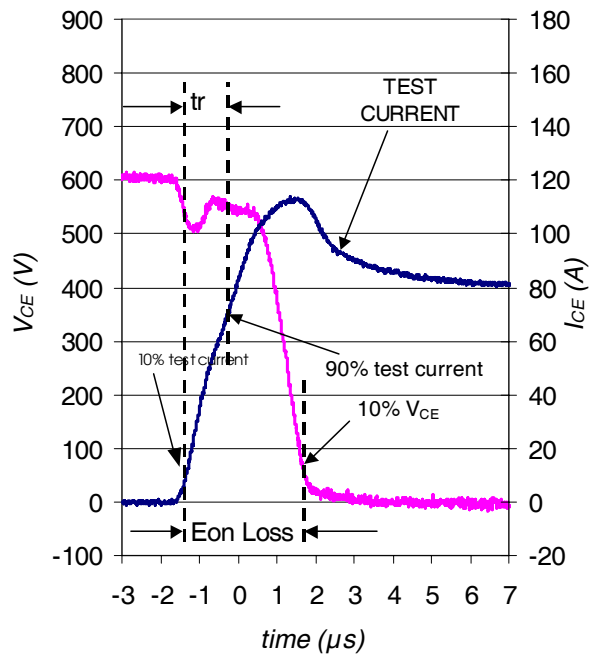
**Fig.C.T.5** - Resistive Load Circuit



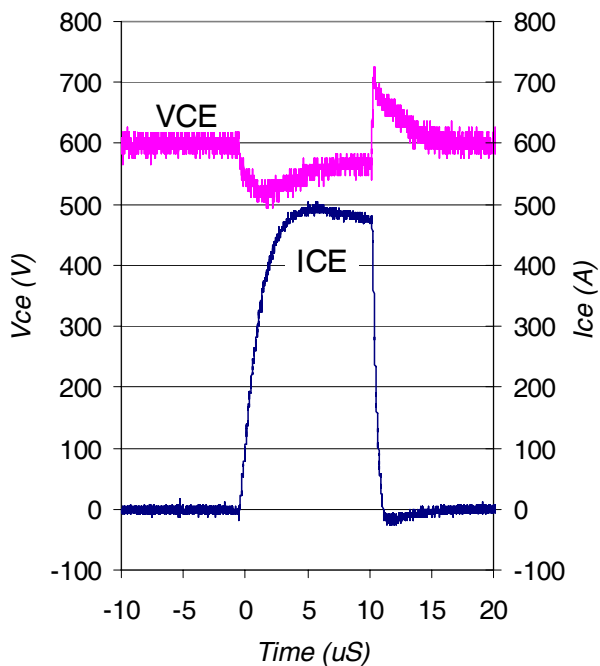
**Fig.C.T.6** - BVCEs Filter Circuit



**Fig. WF1** - Typ. Turn-off Loss Waveform  
@  $T_J = 175^\circ\text{C}$  using Fig. CT.4

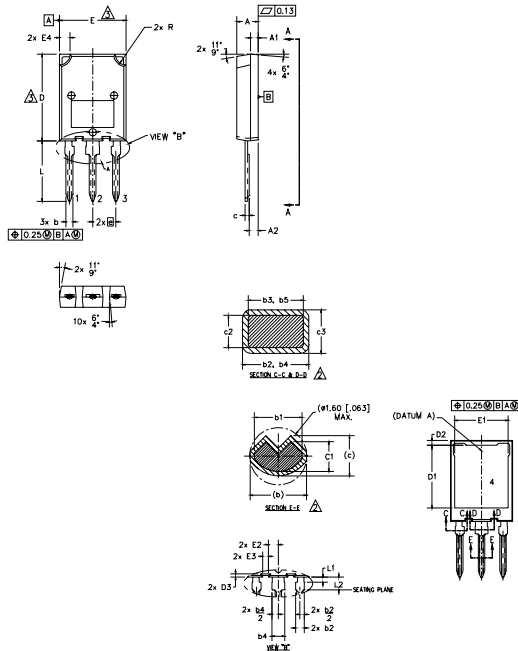


**Fig. WF2** - Typ. Turn-on Loss Waveform  
@  $T_J = 175^\circ\text{C}$  using Fig. CT.4



**Fig. WF3** - Typ. S.C. Waveform  
@  $T_J = 150^\circ\text{C}$  using Fig. CT.3

## Case Outline and Dimensions — Super-247



- NOTES:
1. DIMENSIONING AND TOLERANCING AS PER ASME Y14.5M-1994
  2. DIMENSIONS b1, b3, b5, c1 & c3 APPLY TO BASE METAL ONLY.
  3. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.127 (.005") PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTER EXTREMES OF THE PLASTIC BODY.
  4. ALL DIMENSIONS SHOWN IN MILLIMETERS.
  5. CONTROLLING DIMENSION: MILLIMETER.
  6. OUTLINE CONFORMS TO JEDEC OUTLINE TO-274AA

| SYMBOL | DIMENSIONS  |       |          |      | NOTES |
|--------|-------------|-------|----------|------|-------|
|        | MILLIMETERS |       | INCHES   |      |       |
|        | MIN.        | MAX.  | MIN.     | MAX. |       |
| A      | 4.50        | 5.50  | .177     | .217 |       |
| A1     | 1.45        | 2.15  | .057     | .085 |       |
| A2     | 1.65        | 2.35  | .065     | .093 |       |
| b1     | 1.45        | 1.60  | .054     | .063 |       |
| b2     | 1.40        | 1.50  | .055     | .059 | 2     |
| b3     | 1.95        | 2.35  | .077     | .093 |       |
| b4     | 3.00        | 3.15  | .118     | .124 |       |
| b5     | 2.95        | 3.35  | .116     | .132 | 2     |
| c      | 1.10        | 1.30  | .043     | .051 |       |
| c1     | 0.90        | 1.10  | .035     | .043 | 2     |
| c2     | 0.65        | 0.85  | .026     | .033 |       |
| c3     | 0.50        | 0.70  | .020     | .028 | 2     |
| D      | 19.80       | 20.80 | .780     | .819 | 3     |
| D1     | 15.50       | 16.10 | .610     | .634 |       |
| D2     | 0.70        | 1.30  | .028     | .051 |       |
| D3     | 0.75        | 1.25  | .030     | .049 |       |
| E      | 15.10       | 16.10 | .594     | .634 |       |
| E1     | 13.30       | 13.90 | .524     | .547 |       |
| E2     | 2.25        | 2.70  | .089     | .109 |       |
| E3     | 1.20        | 1.70  | .047     | .067 |       |
| E4     | 2.00        | 3.00  | .079     | .118 |       |
| e      | .545 BSC    |       | .215 BSC |      |       |
| L      | 13.80       | 14.80 | .535     | .583 |       |
| L1     | 1.00        | 1.60  | .039     | .063 |       |
| L2     | 3.85        | 4.25  | .152     | .167 |       |
| R      | 2.00        | 3.00  | .079     | .118 |       |

### LEAD ASSIGNMENTS

#### MOSEFET

1. GATE
2. DRAIN
3. SOURCE
4. DRAIN

#### IGBT

1. GATE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

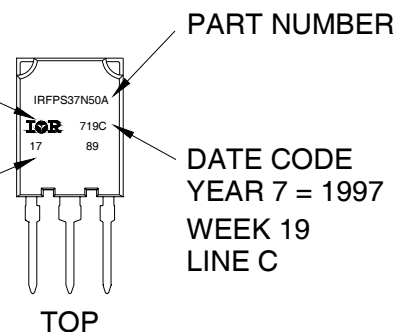
## Super-247 (TO-274AA) Part Marking Information

EXAMPLE: THIS IS AN IRFPS37N50A WITH  
ASSEMBLY LOT CODE 1789  
ASSEMBLED ON WW 19, 1997  
IN THE ASSEMBLY LINE "C"

INTERNATIONAL RECTIFIER  
LOGO

ASSEMBLY LOT CODE

Note: "P" in assembly line position  
indicates "Lead-Free"



PART NUMBER

DATE CODE  
YEAR 7 = 1997  
WEEK 19  
LINE C

TOP

Super-247 package is not recommended for Surface Mount Application.

Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

Data and specifications subject to change without notice.  
This product has been designed and qualified for Industrial market.  
Qualification Standards can be found on IR's Web site.

International  
**IR** Rectifier

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